BYM26AGP THRU BYM26EGP

SINTERED GLASS JUNCTION
FAST SWITCHING PLASTIC RECTIFIER

VOLTAGE：200V to 1000V **CURRENT: 2.3A**

VOLTARISTECH INC.
POWER · PRECISION · INNOVATION

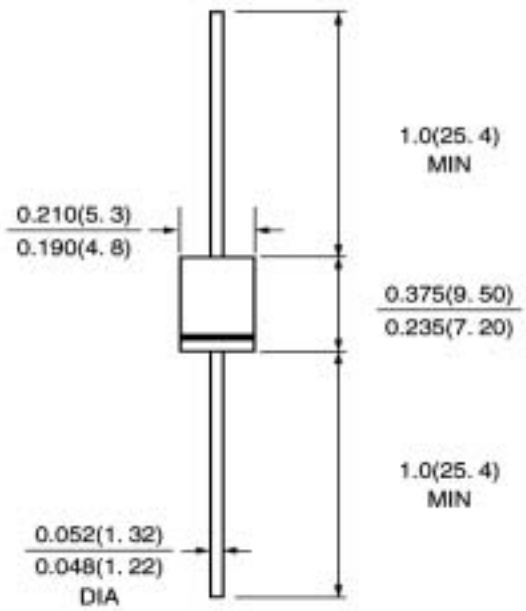
FEATURE

High temperature metallurgically bonded construction
Sintered glass cavity free junction
Capability of meeting environmental standard of MIL-S-19500
High temperature soldering guaranteed
350°C /10sec/0.375"lead length at 5 lbs tension
Low leakage current Typical Ir<0.1μA
Excellent stability
Guaranteed avalanche energy absorption capability

MECHANICAL DATA

Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy
Polarity: color band denotes cathode
Mounting position: any

DO-201AD



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	BYM26 AGP	BYM26 BGP	BYM26 CGP	BYM26 DGP	BYM26 EGP	units
Maximum Recurrent Peak Reverse Voltage	Vrrm	200	400	600	800	1000	V
Maximum RMS Voltage	Vrms	140	280	420	560	700	V
Maximum DC blocking Voltage	Vdc	200	400	600	800	1000	V
Reverse avalanche breakdown voltage at I_R = 0.1 mA	$V_{(BR)R}$ (min)	300	500	700	900	1100	V
Maximum Average Forward Rectified Current 10mm lead length at Ta =55°C	If(av)	2.3					A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load	Ifsm	45					A
Maximum Forward Voltage at rated Forward Current and 25°C I_F=3.0A	Vf	2.65					V
non-repetitive peak reverse avalanche energy (Note 1)	Ersm	10					mJ
Maximum DC Reverse Current Ta =25°C at rated DC blocking voltage Ta =125°C	Ir	10.0 150.0					μA μA
Maximum Reverse Recovery Time (Note 2)	Trr	30			75		nS
Typical Junction Capacitance (Note 3)	Cj	75.0					pF
Typical Thermal Resistance (Note 4)	Rθja	20.0					°C /W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175					°C

Note: 1. L = 120 mH; Tj = Tj max prior to surge; inductive load switched off
2.Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
3.Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
4.Thermal Resistance from Junction to Ambient at 3/8"lead length, P.C. Board Mounted

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Fig.1 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

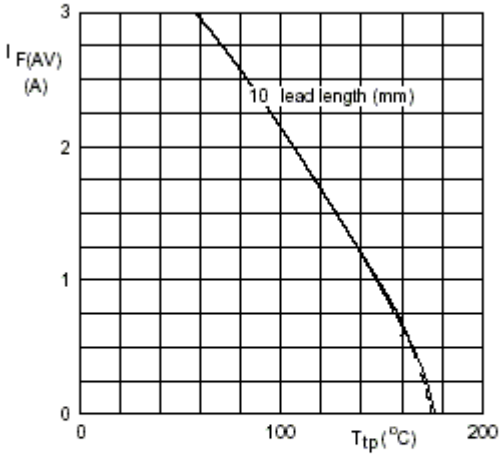

Fig.2 Forward current as a function of forward voltage; maximum values.

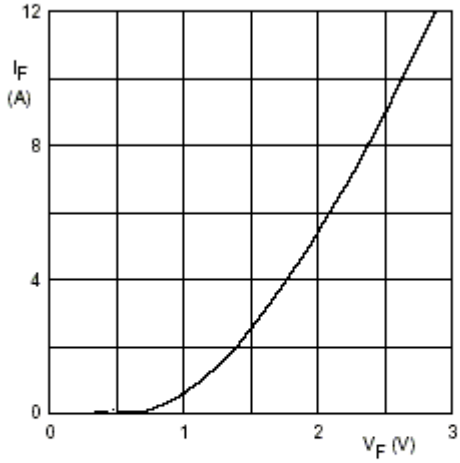

Fig.3 Reverse current as a function of junction temperature; maximum values.

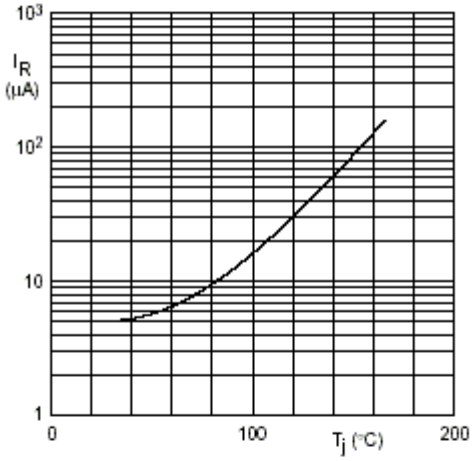
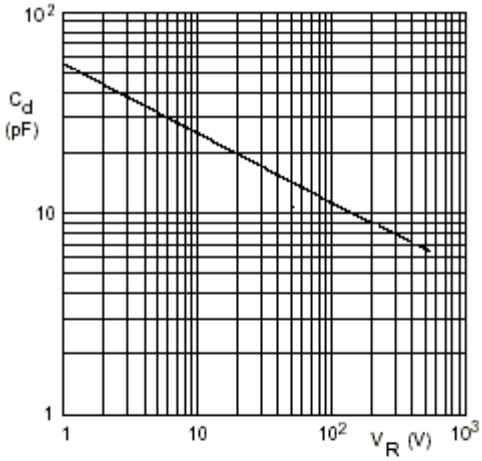
Fig.4 Diode capacitance as a function of reverse voltage; typical values.